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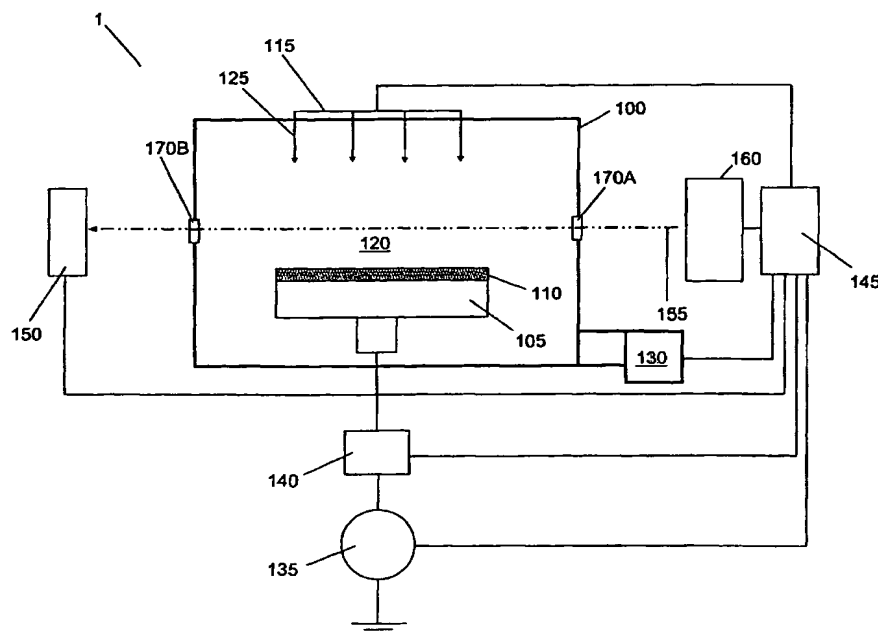
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(54) Title: **PROCESS MONITORING USING INFRARED OPTICAL DIAGNOSTICS**



(57) Abstract: A method and apparatus for real-time monitoring of the substrate and the gaseous process environment in a semiconductor process step is described. The method uses infrared spectroscopy for in-situ analysis of gaseous molecular species in the process region and characterization of adsorbed chemical species on a substrate. The process monitoring can be applied to endpoint- and fault detection in etching and deposition processes, in addition to chamber cleaning and chamber condition steps.

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